

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
23 June 2005 (23.06.2005)

PCT

(10) International Publication Number
WO 2005/057658 A1

(51) International Patent Classification⁷: **H01L 27/12**,
29/786, 21/336, G06K 19/00

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(21) International Application Number:
PCT/JP2004/018978

(22) International Filing Date:
14 December 2004 (14.12.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
2003-417317 15 December 2003 (15.12.2003) JP

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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,
PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

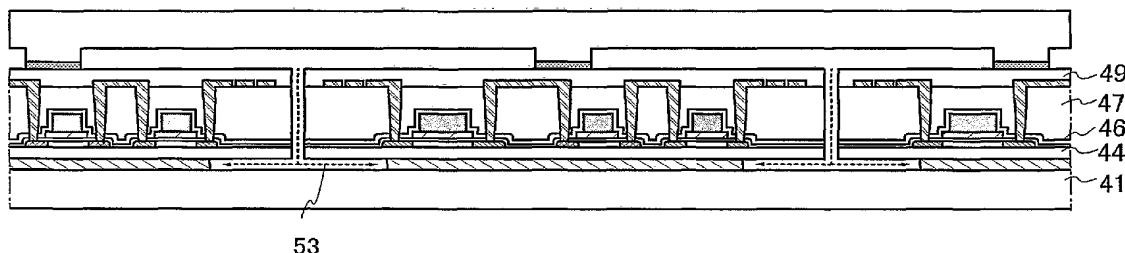
(84) Designated States (unless otherwise indicated, for every
kind of regional protection available): ARIPO (BW, GH,
GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM,
ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM),
European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI,
FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO,
SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN,
GQ, GW, ML, MR, NE, SN, TD, TG).

Published:

— with international search report

For two-letter codes and other abbreviations, refer to the "Guid-
ance Notes on Codes and Abbreviations" appearing at the begin-
ning of each regular issue of the PCT Gazette.

(54) Title: METHOD FOR MANUFACTURING THIN FILM INTEGRATED CIRCUIT DEVICE, NONCONTACT THIN FILM
INTEGRATED CIRCUIT DEVICE AND METHOD FOR MANUFACTURING THE SAME, AND IDTAG AND COIN INCLUD-
ING THE NONCONTACT THIN FILM INTEGRATED CIRCUIT DEVICE



(57) Abstract: To provide a thin film integrated circuit which is mass produced at low cost, a method for manufacturing a thin film
integrated circuit according to the invention includes the steps of: forming a peel-off layer over a substrate; forming a base film over
the peel-off layer; forming a plurality of thin film integrated circuits over the base film; forming a groove at the boundary between
the plurality of thin film integrated circuits; and introducing a gas or a liquid containing halogen fluoride into the groove, thereby
removing the peel-off layer; thus, the plurality of thin film integrated circuits are separated from each other.



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